

isc Silicon NPN Power Transistor

KSD5066

DESCRIPTION

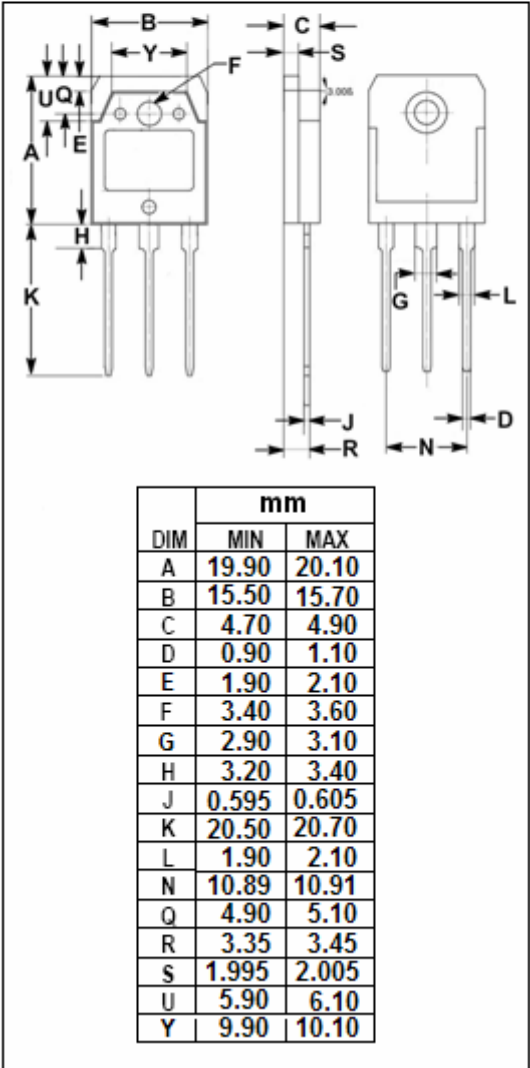
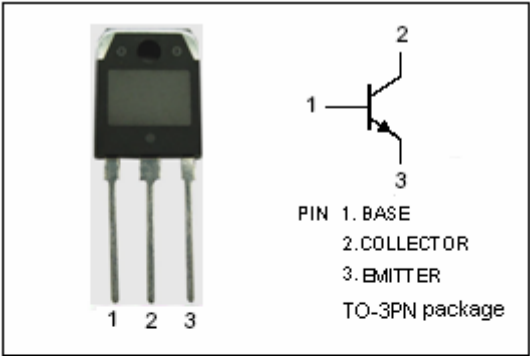
- High Breakdown Voltage-
: $V_{CBO}=1500V$ (Min)
- High Switching Speed
- High Reliability

APPLICATIONS

- Designed for color TV horizontal output applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	5	A
I_{CP}	Collector Current-Peak	16	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	120	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor**KSD5066****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 4\text{A}$; $I_B = 0.8\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 4\text{A}$; $I_B = 0.8\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 800\text{V}$; $I_E = 0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 5\text{V}$; $I_C = 0$			1	mA
h_{FE}	DC Current Gain	$I_C = 1\text{A}$; $V_{CE} = 5\text{V}$	8			
f_T	Current-Gain—Bandwidth Product	$I_C = 1\text{A}$; $V_{CE} = 10\text{V}$		3		MHz
t_f	Fall Time	$I_C = 4\text{A}$, $I_{B1} = 0.8\text{A}$; $I_{B2} = -1.6\text{A}$ $R_L = 50\Omega$; $V_{CC} = 200\text{V}$			0.4	μs